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# The Bloch Oscillating Transistor

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***Abstract*— We introduce a new mesoscopic transistor, which consists of a superconducting island connected to superconducting and normal electrodes via two mesoscopic tunnel junctions. Furthermore, the island is being charged through a resistor. The interplay between Bloch oscillations, single-electron effects and ohmic current leads to a device having a high current gain. The operation and characteristics of the transistor are analyzed with a numerical model.**

***Index Terms*— Bloch oscillations, Single electron tunneling, Mesoscopic tunnel junctions**

As a consequence of improved understanding of phenomena in mesoscopic tunnel junctions and development of fabrication technologies a variety of applications has been suggested and realized during the last two decades. The Single Electron Transistor (SET) [1] has established its position as a basic element of nanotechnology. Recently also the Bloch oscillations [2], [3] in small superconducting tunnel junctions have been utilized [4], [5]. In this paper we introduce a new mesoscopic transistor, the Bloch Oscillating Transistor (BOT). Whereas the SET is more analogous to the Field Effect Transistor (FET), the BOT seems to have characteristics similar to those of a Bipolar Junction Transistor (BJT).

If a mesoscopic Josephson junction is connected to a voltage source via a high impedance, the junction starts to Bloch oscillate. We analyze here a device where an extra junction enables a single electron to tunnel into an island bounded by the Josephson junction, the high impedance, and a single electron junction. We call such a device a single junction BOT (sj BOT) at its equivalent circuit is shown in Fig. 1. The junction #1, characterized by its capacitance $C_1$, connects the normal metal base electrode to the superconducting island via a tunnel resistance $R_{T1}$. The Josephson junction #2 having a capacitance $C_2$ connects the island to the superconducting emitter. The Josephson coupling energy $E_J = \Phi_0 I_{cs}/2\pi$, where $\Phi_0$ is the flux quantum and $I_{cs}$ the critical current, is assumed to be close to the charging energy of the island $E_c = e^2/2C_\Sigma$, where $C_\Sigma = C_1 + C_2$.

We assume here that there is no single electron tunneling through junction #2. We further assume that the tunnel resistance $R_{T1}$ is constant. These criteria are essentially satisfied if $|V_{CC}| < 2\Delta$ and $|V_{CC} - V_B| > \Delta$. Depending on the value of $\Delta$ these criteria are not necessarily satisfied with all voltage values, which has to be taken into account in the design of a practical device. According to the theory of Bloch oscillations [2], the quasicharge $Q_2$ describes the state of the junction #2, if the mesoscopic Josephson junction is sufficiently well isolated. Following the criteria in the theory of the effect of electromagnetic environment on tunnel junctions [6], we find that the bias resistance $R$ should exceed $R_q = h/2e^2$.

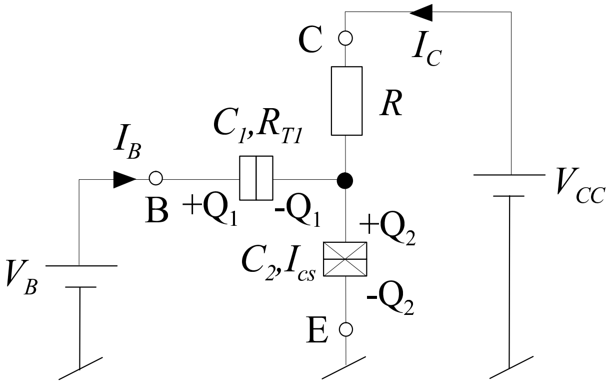

Fig. 1. The equivalent circuit of the single junction Bloch Oscillating Transistor.

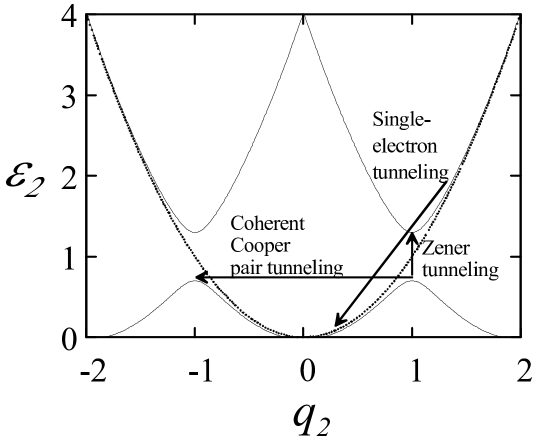

Fig. 2. The energy of the system as a function of the quasicharge.

Since the island is well isolated, the single electron tunneling rates through junction #1 can be obtained using the Orthodox Theory with the local rule. In addition, incoherent Cooper pair tunneling can be neglected. Furthermore, the second order effects, such as cotunneling and Andreév reflections are neglected. Zero temperature is assumed throughout the analyses.

In this paper the quantities are scaled as follows: The charge is expressed in units of $e$, the voltage in $e/C_\Sigma$ the current in $e/R_{T1}C_\Sigma$, the energy in $e^2/2C_\Sigma$, the resistance in $R_{T1}$, the capacitance in $C_\Sigma$, and the time in $R_{T1}C_\Sigma$.

The energy of junction #2 versus the quasicharge forms $2e$-periodic band structure. An energy gap, whose magnitude is the Josephson coupling energy separates the lowest bands (the zeroth and the first band). The gap between bands decreases

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rapidly as a function of band number, so it is reasonable to assume that it is zero between the higher bands. The energy is approximated as [7]

$$\varepsilon_2(q_2) = \frac{1}{2}\left[q_2^2 + (|q_2|-2)^2 \pm \sqrt{\left((|q_2|-2)^2 - q_2^2\right)^2 + \varepsilon_J^2}\right] \tag{1}$$

for the two lowest bands, where $q_2$ is the quasicharge and $\varepsilon_J$ is the Josephson coupling energy. The minus (plus) sign corresponds the zeroth (first) band. For higher bands simple parabolic form is assumed, i.e. $\varepsilon_2(q_2) = q_2^2$. If $|q_2| < e$, the junction is at the zeroth band, if $e < |q_2| < 2e$, the junction is at the first band etc. The energy versus quasicharge $q_2$ is illustrated in Fig. 2.

The charge in the island $q_I = q_2 - q_1$, where $q_1$ is the charge across the junction #1 and $q_2$ is the quasicharge of the junction #2. The (quasi)charges of individual junctions are obtained from $q_I$ with

$$q_1 = \frac{c_1\left(v_B - q_I/c_{2eff}\right)}{1 + c_1/c_{2eff}} \tag{2}$$

$$q_2 = \frac{c_1 v_B + q_I}{1 + c_1/c_{2eff}}. \tag{3}$$

Here $v_B$ is the base voltage, $c_1$ is the capacitance of the first junction and $c_{2eff}$ is the effective capacitance of junction #2, which takes into account the band-structure: $c_{2eff} = q_2/v_2$, where $v_2$ is the voltage across junction #2. The voltage $v_2 = \frac{1}{2}d\varepsilon_2/dq_2$. The effective capacitance $c_{2eff}$ is a function of the quasicharge $q_2$ (and thus also the time) and equals the normal capacitance everywhere else but near the Brillioun zone boundary, where it diverges.

The change of island charge as a function of time is

$$\frac{dq_I}{d\tau} = i_C + \left(\frac{dq_I}{d\tau}\right)_{SET} + \left(\frac{dq_I}{d\tau}\right)_{CPT}, \tag{4}$$

where $i_C = \left(v_{CC} - v_2\right)/r$ is the normalized collector current, $\left(dq_I/d\tau\right)_{SET}$ is due to the single electron tunneling through junction #1 and $\left(dq_I/d\tau\right)_{CPT}$ corresponds to the Cooper pair tunneling through junction #2.

The change of free energy in a single-electron tunnel event is

$$\Delta f_1 = 1 + 2q_I - 2\left(1 - c_1\right)v_b \tag{5}$$

$$\Delta f_2 = 1 - 2q_I + 2\left(1 - c_1\right)v_b, \tag{6}$$

where the index $i = 1$ ($i = 2$) in $\Delta f_i$ refers to tunneling from (to) the island. The tunneling rates are $\gamma_i = -(1/2)\Delta f_i$, if $\Delta f_i < 0$. They are zero otherwise.

As $q_2$ approaches the Brillioun zone boundary at $|q_2| = e$, the junction #2 can either tunnel a Cooper pair (move from $+e$ to $-e$ or from $-e$ to $+e$ within the zeroth or first band) or move to the higher (lower) band via Zener-tunneling. The latter occurs with probability [7]

$$P^Z_{0\leftrightarrow 1} = \exp\left[-\frac{1}{4}\frac{\left(\varepsilon_J\right)^2}{\alpha_t\left|i_C\right|}\right], \tag{7}$$

where $\alpha_t = h/\pi^2 e^2 R_{T1}$.

Parameters used in the simulations are $c_1 = 0.1$, $\varepsilon_J = 0.6$, and $\alpha_t = 0.077$. An example of a set of corresponding values in SI units is $C_2 = 1$ fF, $C_1 = 0.1$ fF, $R_{T1} = 34$ k$\Omega$, and $I_c = 23$ nA.

Figure 3 shows the normalized collector current $i_C$ as a function of the bias voltage $v_{CC}$ for different base voltages $v_B$. The normalized bias resistance $r = 0.5$. For bias voltages $v_{CC} \gtrsim 0.5$ the potential becomes high enough so that Cooper pairs are injected through the Josephson junction. In that range the system Bloch oscillates. Owing to the Zener tunneling the system tends to go the upper energy band and stay there. A single electron tunneling through the junction #1 to the base recovers the system to the lower energy band and the system starts to Bloch oscillate again. This is illustrated in Fig. 4 in the bias point shown in Fig. 3 as an open circle. The share of time the system Bloch oscillates is controlled by the base current. The collector current is thus determined by the base voltage and it is less than the maximum $v_{CC}/r$. Note that in practice $|v_{CC}| \lesssim 2\Delta'$ and $|v_{CC} - v_B| \gtrsim \Delta'$ are not satisfied for all $v_{CC}, v_B$, and thus the transistor cannot be biased at

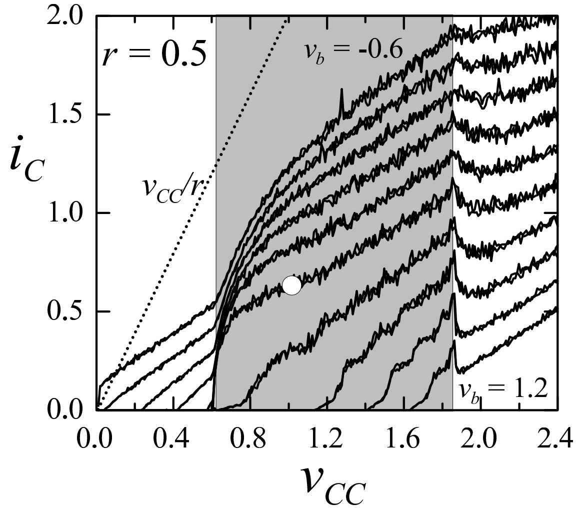

Fig. 3. The collector current as a function of the bias voltage $v_{CC}$ for different base voltages $v_B$. The active region, where the coherent Cooper pair current can be controlled with single electrons tunneling from the base electrode is dark shaded.

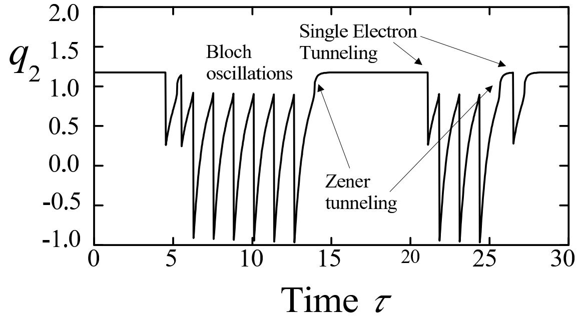

Fig. 4. The quasicharge $q_2$ versus time at a bias point denoted by a white circle in Fig. 3. The Bloch oscillations are interrupted by Zener tunneling, which drives the junction to the first energy band. A single electron tunneling through junction #1 from the base recovers the system to the zeroth band.

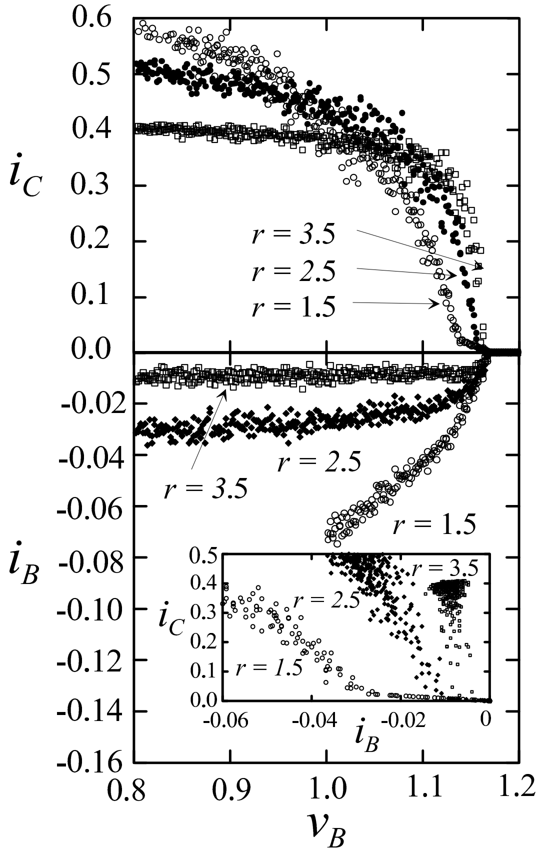

Fig. 5. The normalized collector current $i_C$ and base current $i_B$ as a function of the normalized base voltage $v_B$ at $v_{CC} = 1.7$ for different load resistances $r$. The inset shows the collector current as a function of the base current for $r$ varying from $1.5$ to $3.5$.

all points of operation shown in Figs. 3. The dimensionless energy gap is $\Delta'$.

Figure 5 shows the collector and base currents as a function of the base voltage. The input impedance $r_{in} = dv_B/di_B$ varies from 1 to very high values when $r$ is varied from $1.5$ to $3.5$. The normalized transconductance gain $g'_m = di_C/dv_B$ tends to increase with increasing bias resistance: the maximum $g'_m$ is about 6 for $r = 1.5$ and close to 15 for $r = 3.5$. The maximum current gain $\beta' = di_C/di_B = g'_m r_{in}$ obtained for $r = 1.5$ is about $10$ but when $r = 3.5$ the current gain becomes arbitrarily high as shown in the inset. In SI units $R_{in}$ varies from $R_{T1}$ to arbitrarily high values, the maximum transconductance gain $g_m$ varies from $6/R_{T1}$ to $15/R_{T1}$. Owing to the high input impedance and high current gain the sj BOT can also provide power gain.

In this paper we have described the basic operating principle of the BOT. A single junction BOT where the system is isolated with the bias resistance was analyzed in detail. We were able to show that the Bloch oscillations can be controlled by single electrons tunneling in such a way that the system provides high current gain. We have also analyzed the sj BOT where the charge is injected to the island via an $LR$-circuit.[8] It is also possible that a BOT can be realized by replacing the bias resistance with an other mesoscopic junction. We call such a device a double junction BOT. The noise of the BOT at a finite temperature is limited by the thermal noise of the tunneling resistance $R_{T1}$ and the shot noise related to the current trough the junction #1. According to a brief analysis the noise temperature of the BOT remains below the bath path temperature and the optimal impedance exceeds $R_{T1}$.[8] Since the optimal source resistance is reasonably low at least compared to that of the SET, the BOT may be used as a preamplifier for detectors. An other application for the BOT could be an experiment where a voltage drop across a resistance induced by a current from a single electron pump is compared against a Josephson voltage standard.

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